

Title (en)
Bonding pad used in semiconductor device

Title (de)
Anschlussfläche für Halbleiteranordnung

Title (fr)
Plage de contact utilisée dans un dispositif semi-conducteur

Publication
EP 0395072 B1 19990804 (EN)

Application
EP 90107998 A 19900426

Priority
JP 10591289 A 19890427

Abstract (en)
[origin: EP0395072A2] A polysilicon film (103) is formed on an Si substrate (101) through an insulating oxide film (102), and a composite film (104) constituted by oxide and nitride films is formed on the polysilicon film (103). A polycide layer (105) is formed on the composite film (104), and a metal electrode layer (110) serving as a bonding pad (108) is formed on the polycide layer (105) through a barrier metal layer (109).

IPC 1-7
H01L 23/485

IPC 8 full level
H01L 21/60 (2006.01); **H01L 23/485** (2006.01); **H01L 23/532** (2006.01)

CPC (source: EP KR US)
H01L 21/321 (2013.01 - KR); **H01L 21/60** (2021.08 - KR); **H01L 23/53271** (2013.01 - EP US); **H01L 24/05** (2013.01 - EP US); **H01L 24/48** (2013.01 - EP US); **H01L 2224/02166** (2013.01 - EP US); **H01L 2224/04042** (2013.01 - EP US); **H01L 2224/05073** (2013.01 - EP US); **H01L 2224/05166** (2013.01 - EP US); **H01L 2224/05624** (2013.01 - EP US); **H01L 2224/45124** (2013.01 - EP US); **H01L 2224/48463** (2013.01 - EP US); **H01L 2224/48724** (2013.01 - EP US); **H01L 2224/85205** (2013.01 - EP US); **H01L 2224/85424** (2013.01 - EP US); **H01L 2924/00014** (2013.01 - EP US); **H01L 2924/01005** (2013.01 - EP US); **H01L 2924/01013** (2013.01 - EP US); **H01L 2924/01014** (2013.01 - EP US); **H01L 2924/01022** (2013.01 - EP US); **H01L 2924/01029** (2013.01 - EP US); **H01L 2924/01042** (2013.01 - EP US); **H01L 2924/0105** (2013.01 - EP US); **H01L 2924/01074** (2013.01 - EP US); **H01L 2924/14** (2013.01 - EP US)

Cited by
US5424581A; EP0583877A1; EP0640245A4; EP1061570A4; US6452277B1; US5539244A; EP0490506A1; US5250760A; US6583506B1

Designated contracting state (EPC)
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